

P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR
Features

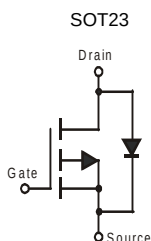
- Low $R_{DS(ON)}$
 - 72m Ω @ $V_{GS} = -4.5V$
 - 108m Ω @ $V_{GS} = -2.7V$
 - 123m Ω @ $V_{GS} = -2.5V$
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

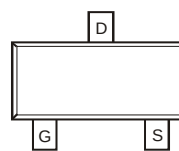
- Case: SOT23
- Case Material - Molded Plastic, "Green" Molding Compound.
UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper
Leadframe. Solderable per MIL-STD-202, Method 208 (B3)
- Terminal Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



Top View



Internal Schematic

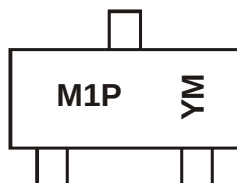


Top View

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2123LQ-7	SOT23	3,000/Tape & Reel
DMP2123LQ-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. For more information, please refer to http://www.diodes.com/product_compliance_definitions.html.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information


M1P = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: C = 2015)
 M = Month (ex: 9 = September)

Date Code Key

Year	2007	...	2015	2016	2017	2018	2019	2020	2021	2022	2023
Code	U	...	C	D	E	F	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current (Note 6) Continuous T _A = +25°C T _A = +70°C	I _D	-3.0 -2.4	A
Pulsed Drain Current (Note 7)	I _{DM}	-15	A
Body-Diode Continuous Current (Note 6)	I _S	-2.0	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 6); Steady-State	R _{θJA}	90	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV _{DS}	-20	—	—	V	I _D = -250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Body Leakage Current	I _{GSS}	—	—	±100	nA	V _{DS} = 0V, V _{GS} = ±12V
Gate Threshold Voltage	V _{GS(TH)}	-0.6	—	-1.25	V	V _{DS} = V _{GS} , I _D = -250μA
On State Drain Current (Note 8)	I _{D(ON)}	-15	—	—	A	V _{GS} = -4.5V, V _{DS} = -5V
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}	—	51 87 99	72 108 123	mΩ	V _{GS} = -4.5V, I _D = -3.5A V _{GS} = -2.7V, I _D = -3.0A V _{GS} = -2.5V, I _D = -2.6A
Forward Transconductance (Note 8)	g _{FS}	—	7.3	—	S	V _{DS} = -10V, I _D = -3.0A
Diode Forward Voltage (Note 6)	V _{SD}	—	-0.79	-1.26	V	I _S = -1.7A, V _{GS} = 0V
Maximum Body-Diode Continuous Current (Note 6)	I _S	—	—	-1.7	A	—
DYNAMIC PARAMETERS (Note 9)						
Total Gate Charge	Q _g	—	7.3	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -3.0A
Gate-Source Charge	Q _{gs}	—	2.0	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -3.0A
Gate-Drain Charge	Q _{gd}	—	1.9	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -3.0A
Turn-On Delay Time	t _{D(ON)}	—	12	—	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _L = 10Ω, R _G = 6Ω
Turn-On Rise Time	t _R	—	20	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	38	—	ns	
Turn-Off Fall Time	t _F	—	41	—	ns	
Input Capacitance	C _{iss}	—	443	—	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	128	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	101	—	pF	

- Notes:
6. Device mounted on 1" x 1", FR-4 PC board with 2 oz. copper and test pulse width t ≤ 10s.
 7. Repetitive Rating, pulse width limited by junction temperature.
 8. Test pulse width t = 300μs.
 9. Guaranteed by design. Not subject to product testing.

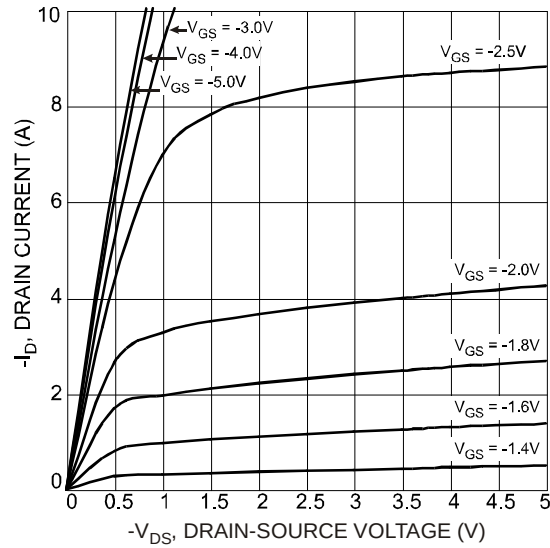


Fig. 1 Typical Output Characteristics

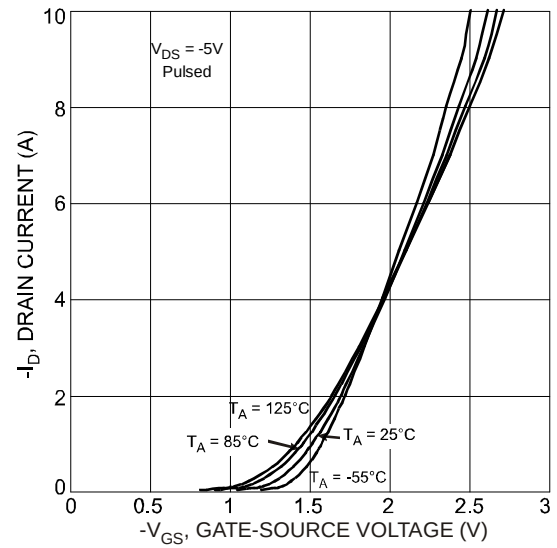


Fig. 2 Typical Transfer Characteristics

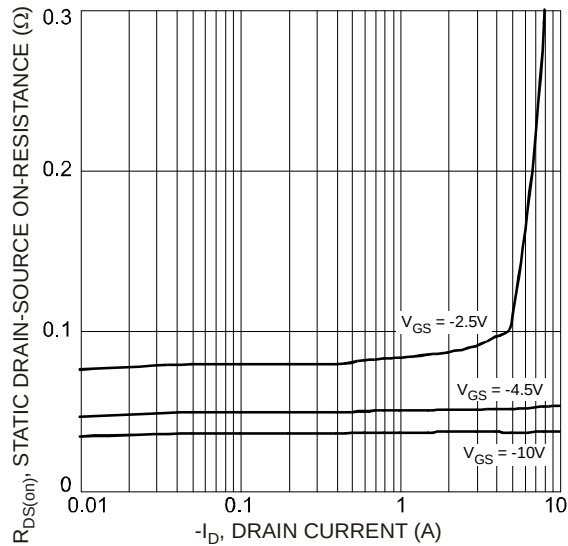


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

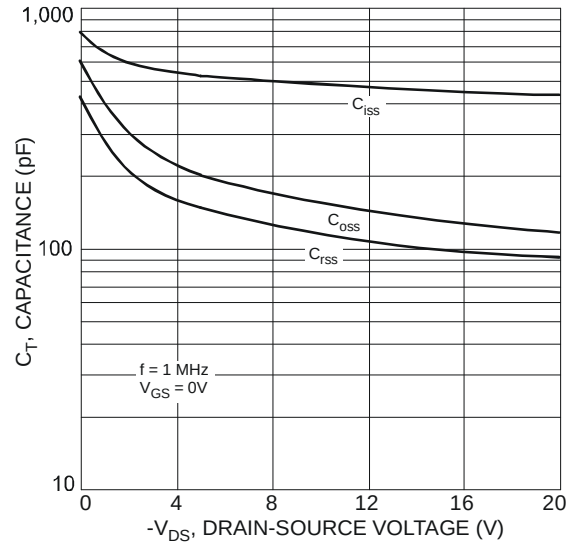


Fig. 4 Typical Total Capacitance

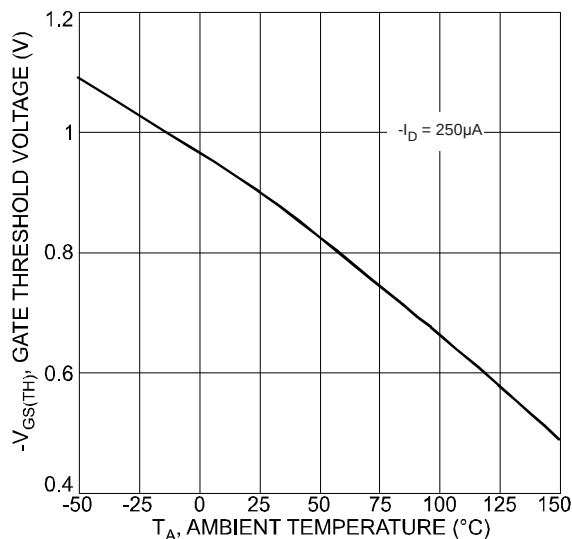


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

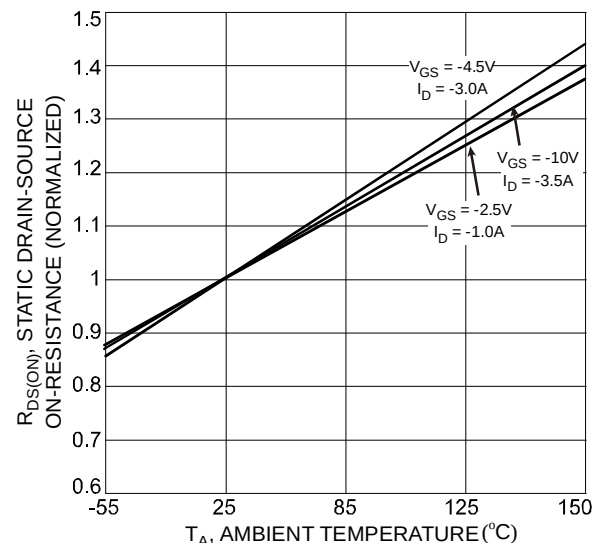


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

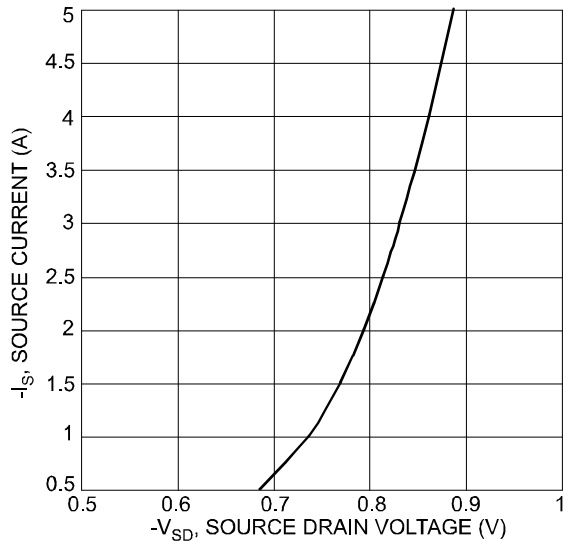


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

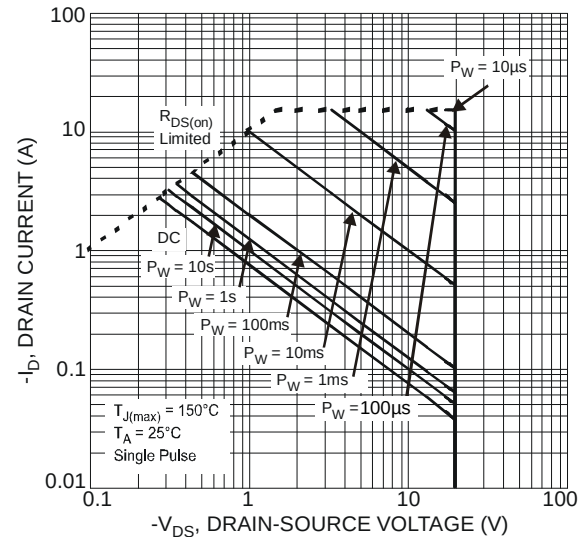
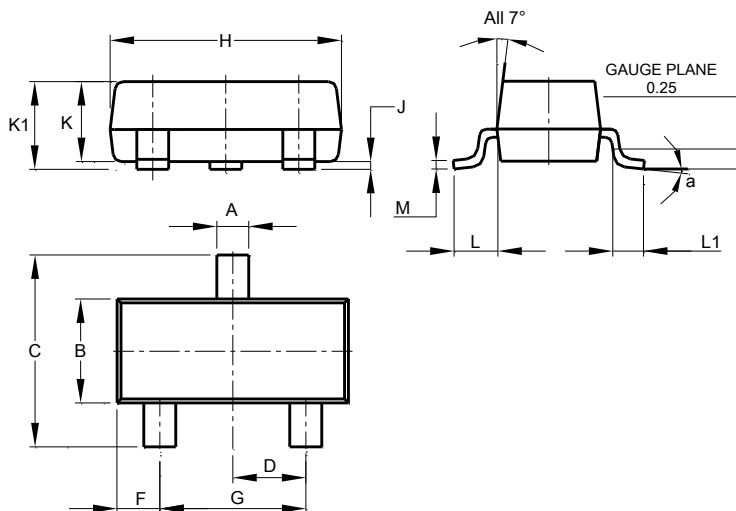


Fig. 8 SOA, Safe Operation Area

Package Outline Dimensions

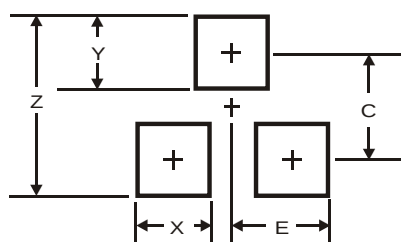
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9